CLEAN VERSION OF PENDING CLAIMS:

1. (Amended) A thyristor made of a semiconductor material, said thyristor comprising:

a first emitter region of a first conductivity type;

a first contact region contacting said first emitter region;

a first base region of a second conductivity type disposed on said first emitter region opposite the first contact region;

a second base region of the first conductivity type disposed on said first base region;

a second emitter region of the second conductivity type disposed on said second base region;

a second contact region contacting said second emitter region opposite said second base region;

at least one driver stage having a third emitter region of the first conductivity type formed in said second base region and isolated from said first emitter region, said driver stage capable of amplifying a control current fed into the first base region; and

an electrically conducting layer electrically connecting the first base region with the third emitter region;

wherein the thyristor includes at least one of the following features:

said third emitter region and said first base region located beneath said layer of said driver stage together with said second

base region form a transistor having a gain factor (α') that is greater than a gain factor (α) of a transistor formed beneath the first electrode of the thyristor by the first emitter region, the first base region and the second base region, and

said first base region, said first base region and said second base region located beneath said layer of said driver stage form a transistor having a gain factor (α') that is greater than a gain factor (α) of a transistor formed beneath the first electrode of the thyristor by the first base region, the second base region and the second emitter region, and

short circuits are formed in the second base, said short circuits connecting the second base and the second contact region to one another, and wherein an electrical conductivity of the short circuits formed below the electrically conducting layer is smaller than an electrical conductivity of the short circuits formed beneath the first contact region.

2. (Amended) The thyristor of claim 1, the second base further including a stop zone of the first conductivity type.

3. (Amended) The thyristor of claim 2, wherein a doping level of the stop zone in a region located beneath the electrically conducting layer of the at least one driver stage is smaller than a doping level in a region located beneath the first contact region.

4. (Twice amended) the thyristor of claim 2, wherein a doping level of the stop zone in a region located beneath the electrically conducting layer of the at least one driver stage is greater than in a region located beneath a location adapted to supply the control current to the first base region.

5. (Twice amended) The thyristor of claim 1, wherein the short circuits formed beneath the electrically conducting layer of the driver stage are at a greater distance from one another than the short circuits formed beneath the first contact region.

6. (Twice amended) The thyristor of claim 1, further comprising a diode electrically connected to the second contact region.

7. (New) The thyristor of claim 1, wherein the short circuits formed beneath the electrically conducting layer of the driver stage have a smaller diameter than the short circuits formed beneath the first contact region.

8. (New) The thyristor of claim 1, wherein the first conductivity type is n-type and the second conductivity type is p-type.

9. (New) The thyristor of claim 1, wherein the first conductivity type is p-type and the second conductivity type is n-type.